# **MMBF2202PT1**

# **Power MOSFET** 300 mAmps, 20 Volts

# P-Channel SC-70/SOT-323

These miniature surface mount MOSFETs low RDS(on) assure minimal power loss and conserve energy, making these devices ideal for use in small power management circuitry. Typical applications are dc-dc converters, power management in portable and battery-powered products such as computers, printers, PCMCIA cards, cellular and cordless telephones.

#### **Features**

- Low R<sub>DS(on)</sub> Provides Higher Efficiency and Extends Battery Life
- Miniature SC-70/SOT-323 Surface Mount Package Saves Board Space
- AEC Qualified
- PPAP Capable
- Pb-Free Package is Available

### MAXIMUM RATINGS (T<sub>J</sub> = 25°C unless otherwise noted)

Rating	Symbol	Value	Unit
Drain-to-Source Voltage	V <sub>DSS</sub>	20	Vdc
Gate-to-Source Voltage - Continuous	V <sub>GS</sub>	± 20	Vdc
	I <sub>D</sub> I <sub>D</sub> I <sub>DM</sub>	300 240 750	mAdc
Total Power Dissipation @ T <sub>A</sub> = 25°C (Note 1) Derate above 25°C	P <sub>D</sub>	150 1.2	mW mW/°C
Operating and Storage Temperature Range	T <sub>J</sub> , T <sub>stg</sub>	- 55 to 150	°C
Thermal Resistance, Junction-to-Ambient	$R_{\theta JA}$	833	°C/W
Maximum Lead Temperature for Soldering Purposes, for 10 seconds	TL	260	°C

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

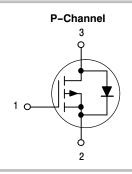
1. Mounted on G10/FR4 glass epoxy board using minimum recommended footprint.



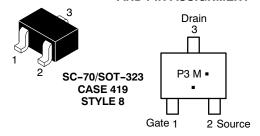
## ON Semiconductor®

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# 300 mAMPS, 20 VOLTS $R_{DS(on)} = 2.2 \Omega$



#### MARKING DIAGRAM AND PIN ASSIGNMENT



РЗ = Specific Device Code

М = Date Code\*

= Pb-Free Package (Note: Microdot may be in either location)

\*Date Code orientation may vary depending upon manufacturing location.

#### **ORDERING INFORMATION**

Device	Package	Shipping <sup>†</sup>
MMBF2202PT1	SC-70/ SOT-323	3000 Tape & Reel
MMBF2202PT1G	SC-70/ SOT-323 (Pb-Free)	3000 Tape & Reel

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

Preferred devices are recommended choices for future use and best overall value.

### MMBF2202PT1

## $\textbf{ELECTRICAL CHARACTERISTICS} \ (T_A = 25^{\circ}\text{C unless otherwise noted})$

Char	Symbol	Min	Тур	Max	Unit	
OFF CHARACTERISTICS						
Drain-to-Source Breakdown Voltage (V <sub>GS</sub> = 0 Vdc, I <sub>D</sub> = 10 μA)	V <sub>(BR)DSS</sub>	20	_	_	Vdc	
Zero Gate Voltage Drain Current $(V_{DS} = 16 \text{ Vdc}, V_{GS} = 0 \text{ Vdc})$ $(V_{DS} = 16 \text{ Vdc}, V_{GS} = 0 \text{ Vdc}, T_J = 0 \text{ Vdc})$	= 125°C)	I <sub>DSS</sub>	- -	- -	1.0 10	μAdc
Gate-Body Leakage Current (V <sub>GS</sub> =	± 20 Vdc, V <sub>DS</sub> = 0)	I <sub>GSS</sub>	-	-	±100	nAdc
ON CHARACTERISTICS (Note 2)			•	•	•	•
Gate Threshold Voltage $(V_{DS} = V_{GS}, I_D = 250 \mu Adc)$		V <sub>GS(th)</sub>	1.0	1.7	2.4	Vdc
Static Drain-to-Source On-Resistar ( $V_{GS}$ = 10 Vdc, $I_D$ = 200 mAdc) ( $V_{GS}$ = 4.5 Vdc, $I_D$ = 50 mAdc)	r <sub>DS(on)</sub>	- -	1.5 2.0	2.2 3.5	Ω	
Forward Transconductance (V <sub>DS</sub> = 1	9FS	-	600	-	mMhos	
DYNAMIC CHARACTERISTICS		·				
Input Capacitance	(V <sub>DS</sub> = 5.0 V)	C <sub>iss</sub>	_	50	-	pF
Output Capacitance	(V <sub>DS</sub> = 5.0 V)	C <sub>oss</sub>	-	45	-	
Transfer Capacitance	(V <sub>DG</sub> = 5.0 V)	C <sub>rss</sub>	-	20	-	
SWITCHING CHARACTERISTICS (Note 3)						<u>,                                    </u>
Turn-On Delay Time		t <sub>d(on)</sub>	_	2.5	_	ns
Rise Time	$(V_{DD} = -15 \text{ Vdc},$	t <sub>r</sub>	-	1.0	-	
Turn-Off Delay Time	$R_L = 75 \Omega$ , $I_D = 200 \text{ mAdc}$ , $V_{GEN} = -10 \text{ V}$ , $R_G = 6.0 \Omega$ )	t <sub>d(off)</sub>	-	16	-	
Fall Time		t <sub>f</sub>	-	8.0	-	
Gate Charge (See Figure 5)	$(V_{DS} = 16 \text{ V}, V_{GS} = 10 \text{ V}, I_{D} = 200 \text{ mA})$	Q <sub>T</sub>	-	2700	-	pC
SOURCE-DRAIN DIODE CHARACT	TERISTICS		•	•	•	•
Continuous Current	Is	-	_	0.3	Α	
Pulsed Current	I <sub>SM</sub>	-	-	0.75		
Forward Voltage (Note 3)	V <sub>SD</sub>	-	1.5	-	V	

<sup>2.</sup> Pulse Test: Pulse Width ≤ 300 μs, Duty Cycle ≤ 2%.

## **TYPICAL CHARACTERISTICS**

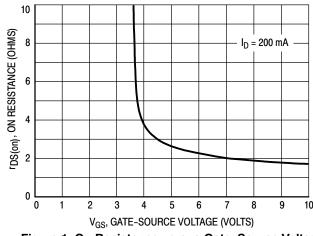


Figure 1. On Resistance versus Gate-Source Voltage

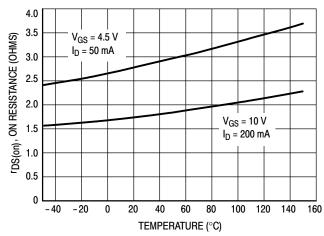


Figure 2. On Resistance versus Temperature

<sup>3.</sup> Switching characteristics are independent of operating junction temperature.

### MMBF2202PT1

### **TYPICAL CHARACTERISTICS**

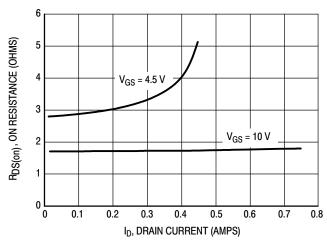


Figure 3. On Resistance versus Drain Current

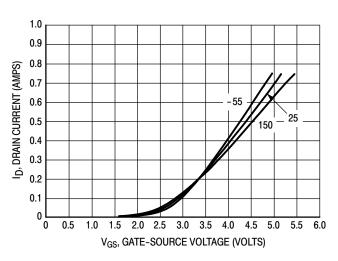


Figure 4. Transfer Characteristics

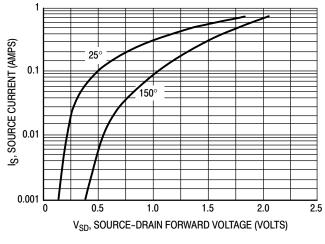


Figure 5. Source-Drain Forward Voltage

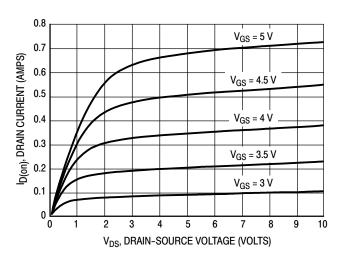


Figure 6. On Region Characteristics

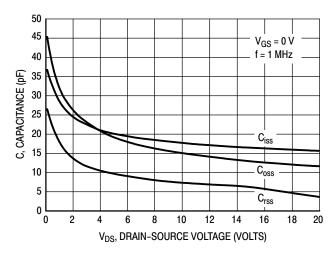


Figure 7. Capacitance Variation





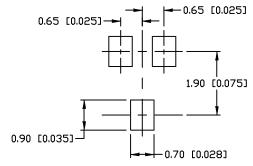
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**DATE 07 OCT 2021** 

#### NOTES:

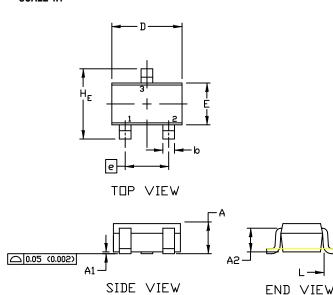
- 1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1982.
- 2. CONTROLLING DIMENSION: INCH

	MILLIMETERS				INCHES		
DIM	MIN.	N□M. MAX.		MIN.	N□M.	MAX.	
Α	0.80	0.90	1.00	0.032	0.035	0.040	
A1	0.00	0.05	0.10	0.000	0.002	0.004	
A2		0.70 REF			0.028 BSC		
b	0.30	0.35	0.40	0.012	0.014	0.016	
С	0.10	0.18	0.25	0.004	0.007	0.010	
D	1.80	2.10	2.20	0.071	0.083	0.087	
Ε	1.15	1.24	1.35	0.045	0.049	0.053	
e	1.20	1.30	1.40	0.047	0.051	0.055	
e1	0.65 BSC				0.026 BS	C	
L	0.20	0.38	0.56	0.008	0.015	0.022	
HE	2.00	2.10	2.40	0.079	0.083	0.095	



For additional information on our Pb-Free strategy and soldering details, please download the IIN Semiconductor Soldering and Mounting Techniques Reference Manual, SILDERRM/D.

SOLDERING FOOTPRINT



# GENERIC MARKING DIAGRAM



XX = Specific Device Code

M = Date Code

■ = Pb-Free Package

\*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "•", may or may not be present. Some products may not follow the Generic Marking.

STYLE 1: CANCELLED	STYLE 2: PIN 1. ANODE 2. N.C. 3. CATHODE	STYLE 3: PIN 1. BASE 2. EMITTER 3. COLLECTOR	STYLE 4: PIN 1. CATHODE 2. CATHODE 3. ANODE	STYLE 5: PIN 1. ANODE 2. ANODE 3. CATHODE	
STYLE 6:	STYLE 7:	STYLE 8:	STYLE 9:	STYLE 10:	STYLE 11:
PIN 1. EMITTER	PIN 1. BASE	PIN 1. GATE	PIN 1. ANODE	PIN 1. CATHODE	PIN 1. CATHODE
2. BASE	2. EMITTER	2. SOURCE	2. CATHODE	2. ANODE	2. CATHODE
3. COLLECTOR	3. COLLECTOR	3. DRAIN	3. CATHODE-ANODE	3. ANODE-CATHODE	3. CATHODE

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